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(54) **Method of fabricating semiconductor laser**

(57) In a self-aligned structure semiconductor laser in which a pair of optical guide layers (23, 28) are respectively formed on both faces of an active layer (25), the optical guide layers having a bandgap which is wider than that of the active layer (25), a pair of cladding layers (22, 29) are formed so as to sandwich the active layer (25) and the optical guide layers (23, 28), the cladding layers having a bandgap which is wider than bandgap of the optical guide layers (23, 28), a pair of carrier blocking layers (24, 26) are respectively formed between the

active layer (25) and the optical guide layers (23, 28), the carrier blocking layers having a bandgap which is wider than bandgaps of the active layer (25) and the optical guide layers (23, 28), and a current blocking layer (27) having a stripe-like window is embedded in at least one of the optical guide layers (23, 28), the current blocking layer (27) is formed by selective growth.

In this way, a window of a current blocking layer can be accurately formed and the fabrication yield can be improved while avoiding maleffects on other layers.

FIG. 1A

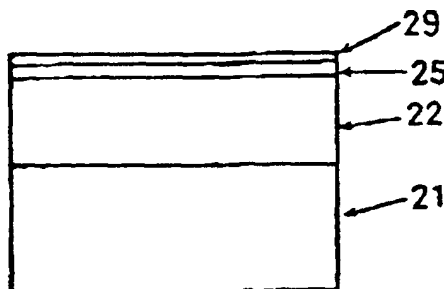


FIG. 1B

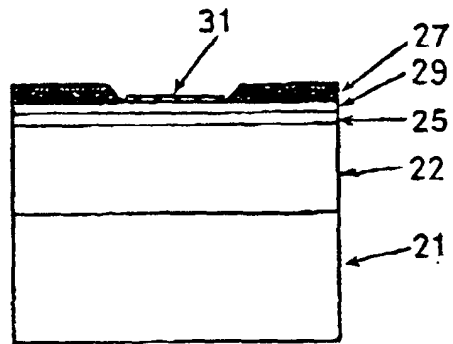
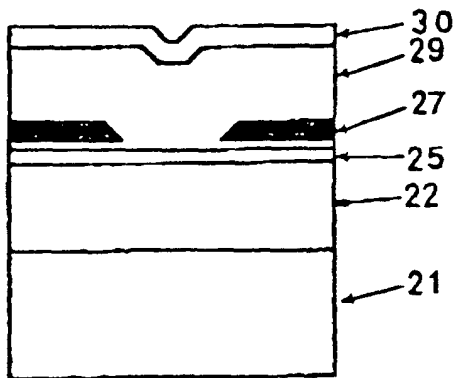


FIG. 1C





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EUROPEAN SEARCH REPORT

Application Number
EP 98 30 7590

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Y	* column 1, line 12 - line 15 * * paragraph [0111]; figures 3,4 * ---	2	
Y	HASHIMOTO T ET AL: "REDUCTION OF BEAM DIVERGENCE ANGLE BY LOW-REFRACTIVE-INDEX LAYERS INTRODUCED TO REAL-REFRACTIVE-INDEX-GUIDED GAALAS HIGH-POWER LASER DIODES" JAPANESE JOURNAL OF APPLIED PHYSICS,JP,PUBLICATION OFFICE JAPANESE JOURNAL OF APPLIED PHYSICS. TOKYO, vol. 36, no. 5A, 1 May 1997 (1997-05-01), pages 2676-2680, XP000732382 ISSN: 0021-4922 * paragraph [02.2]; figure 2 * ---	2	
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The present search report has been drawn up for all claims			
Place of search		Date of completion of the search	Examiner
THE HAGUE		9 August 2000	Hervé, D
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X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document		T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document	

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The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 9 August 2000	Examiner Hervé, D
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**ANNEX TO THE EUROPEAN SEARCH REPORT
ON EUROPEAN PATENT APPLICATION NO.**

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This annex lists the patent family members relating to the patent documents cited in the above-mentioned European search report.
The members are as contained in the European Patent Office EDP file on
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